

# EECS 151/251A

## Discussion 7

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10/12/21, 10/13/21, 10/18/21

# Administrativa

- Slip week for labs – lab 5 due **10/15, 11:59pm**
- Homework 5 posted, due **10/15, 11:59pm**

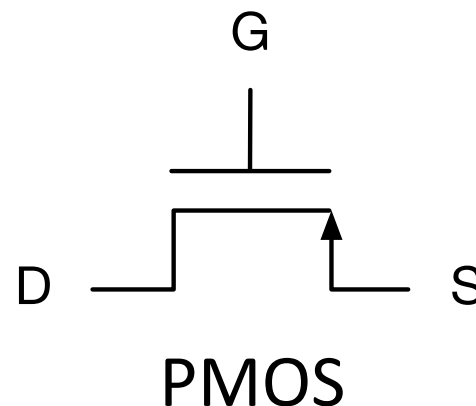
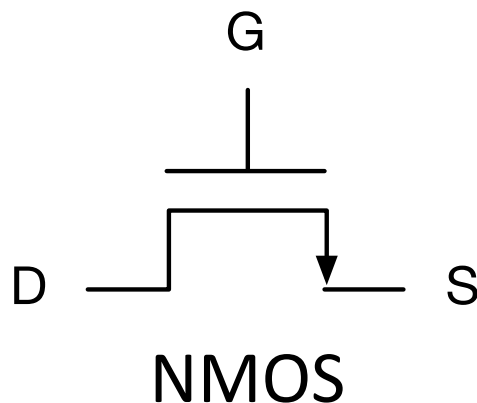
# Agenda

- Transistor as a switch model
- Inverter
- Complementary CMOS gates

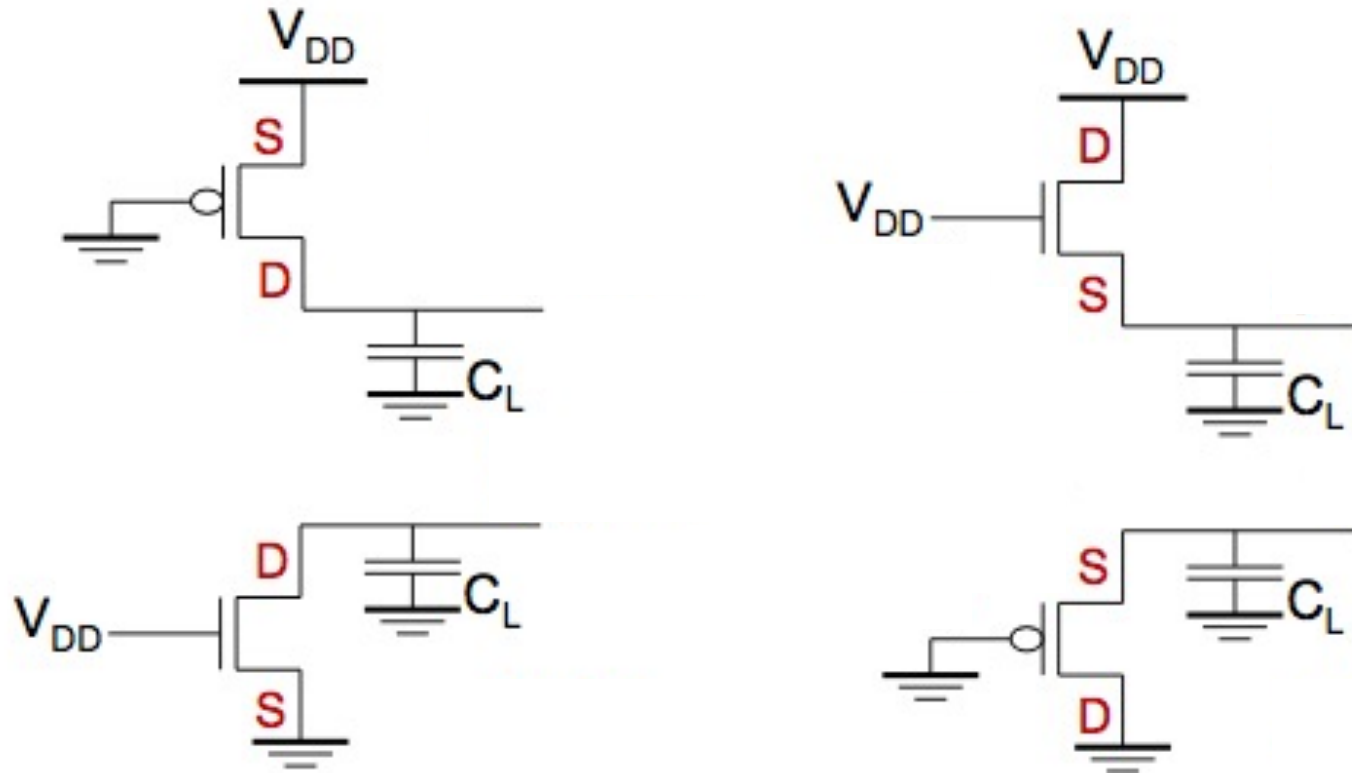
# Transistor Models

# Transistor review

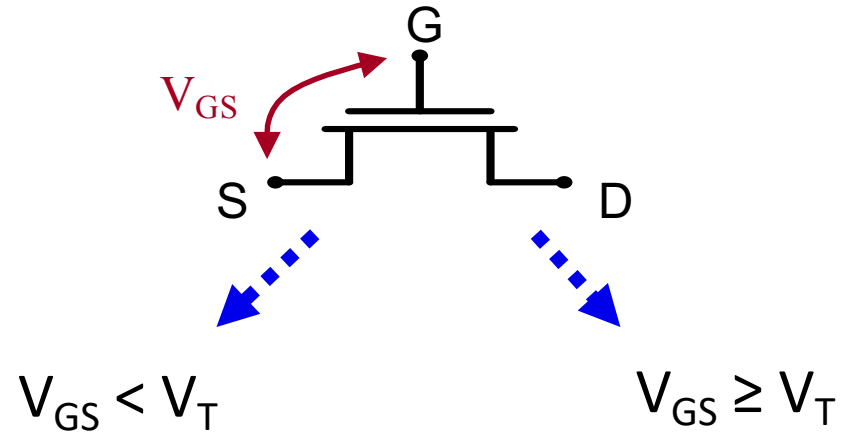
- CMOS
  - Complementary Metal Oxide Semiconductor (FET)
- Transistor basics
  - N-type or P-type – based on carrier type
  - Potential between source and gate forms a “channel”
  - Channel connects source and drain
  - Defined by “threshold” voltage  $V_{th}$



# Transistors connect outputs to supplies



# Transistors as switches

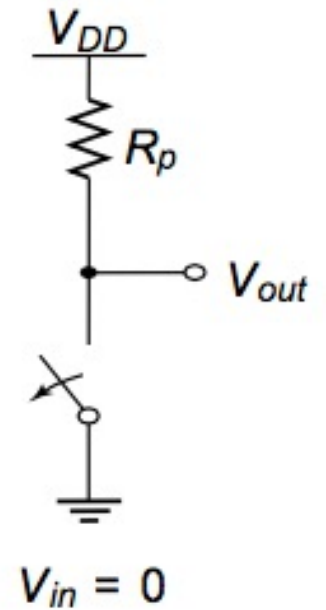
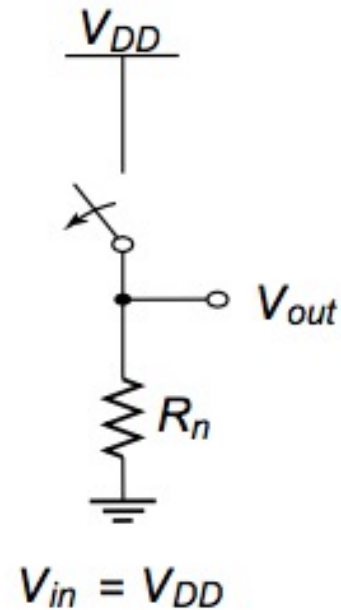
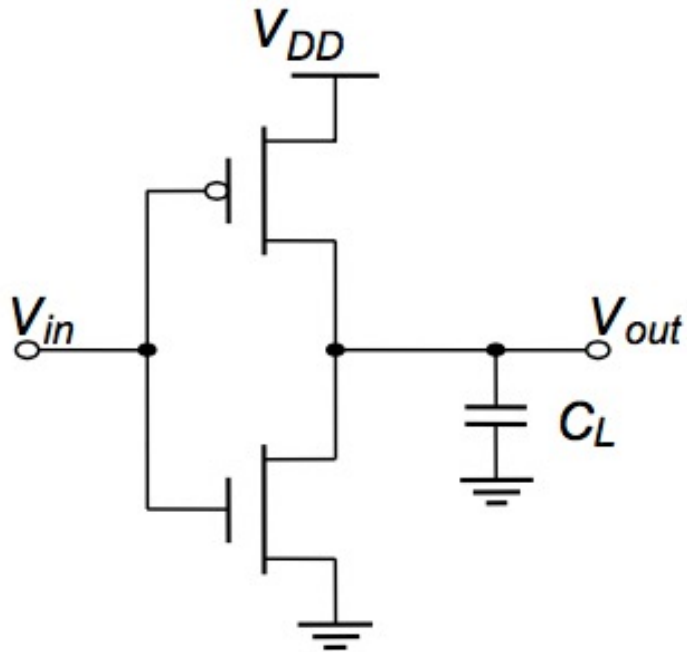


# Inverters



# CMOS inverter

Most basic CMOS logic gate



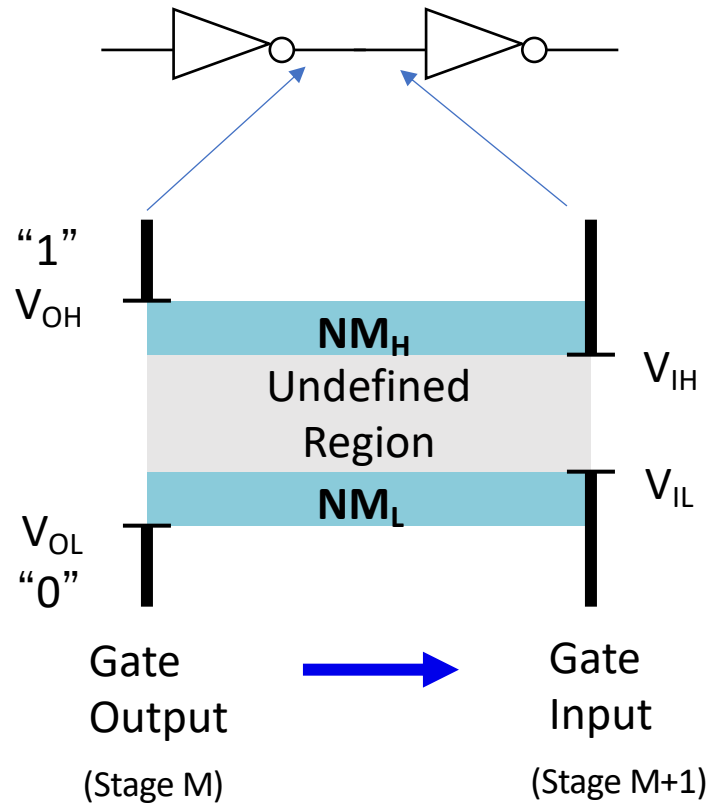
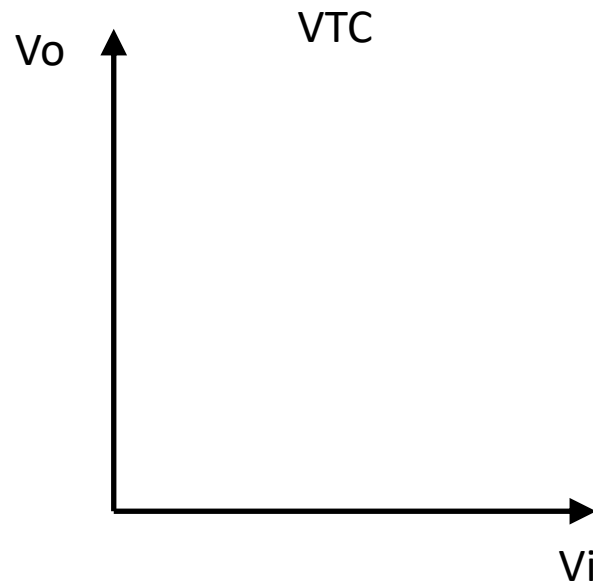
# Inverter noise margins

Noise margin high:

$$NM_H = V_{OH} - V_{IH}$$

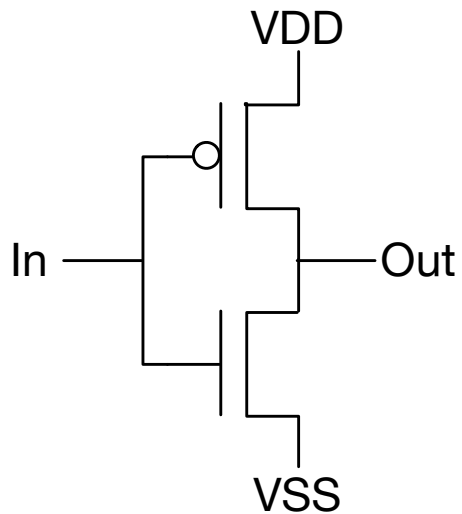
Noise margin low:

$$NM_L = V_{IL} - V_{OL}$$



# Static complementary CMOS

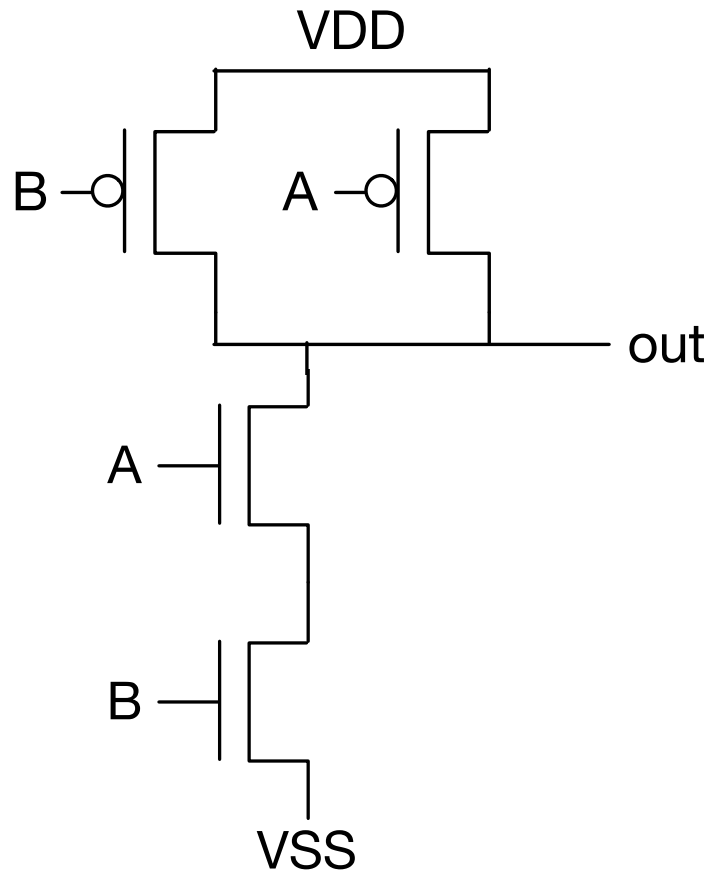
# Static gates



# Static complementary CMOS

# NAND gate

# NAND gate



- Notice that the PUN and PDN are “opposite”
  - Meaning serial vs. parallel
  - This concept known as “duality”
- Also notice that the gate was inverting
  - How do we make an AND? (next slides)
- Easiest way to make a gate is to define the PDN first
  - Make the PUN by flipping the branches of the PDN

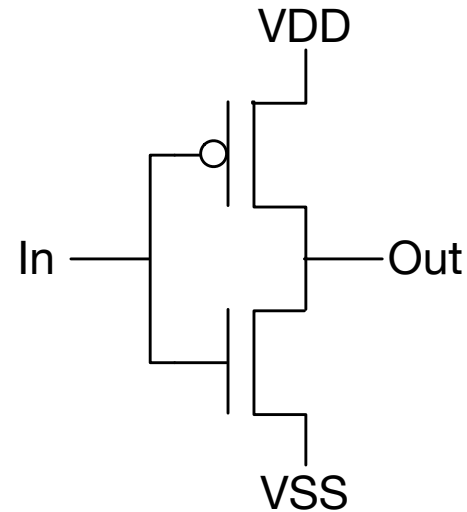
# XNOR gate



# AND gate

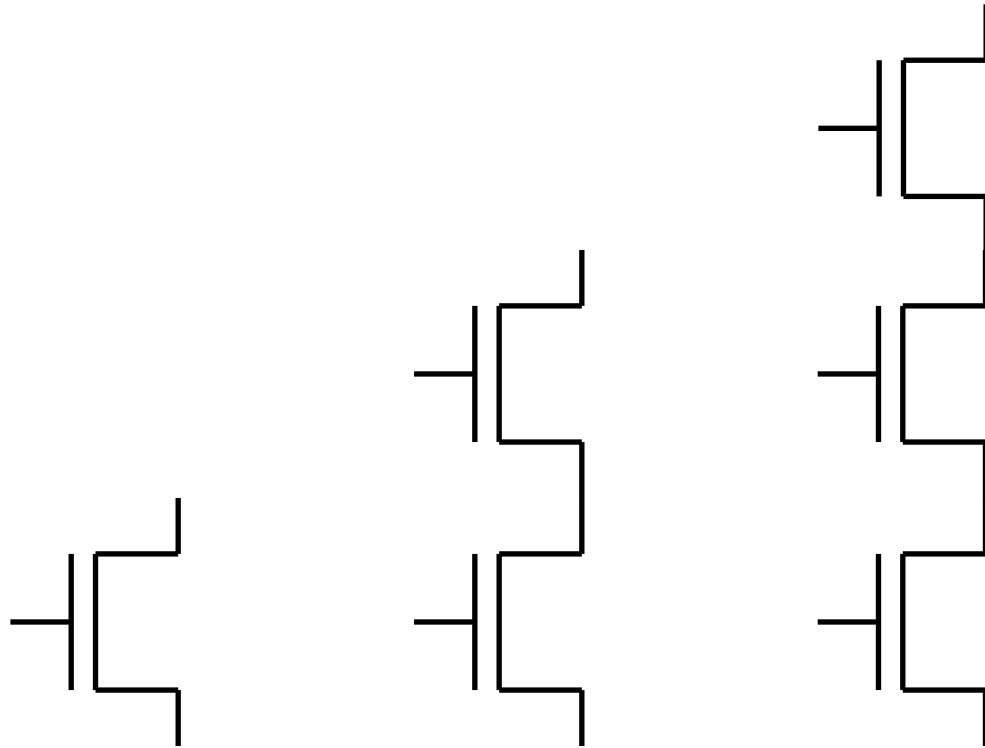
# CMOS gate sizing

- Choosing the width of a transistor (typically use minimum length)
- Minimum sized inverter:

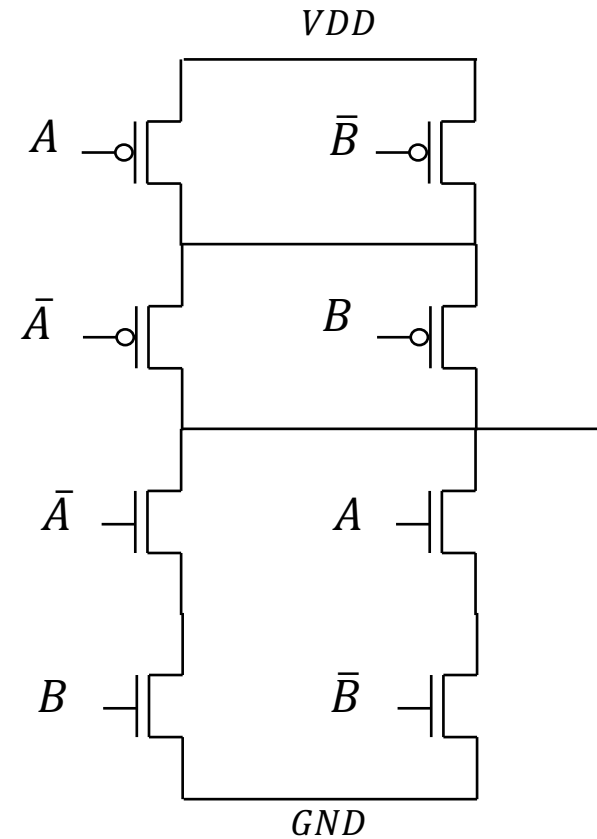


- **Unless otherwise stated**, complex gates should:
  - Have equal pull-up and pull-down resistances
  - Pull-up and pull-down resistances equivalent to minimum sized inverter

# Transistor stacks – R vs. W

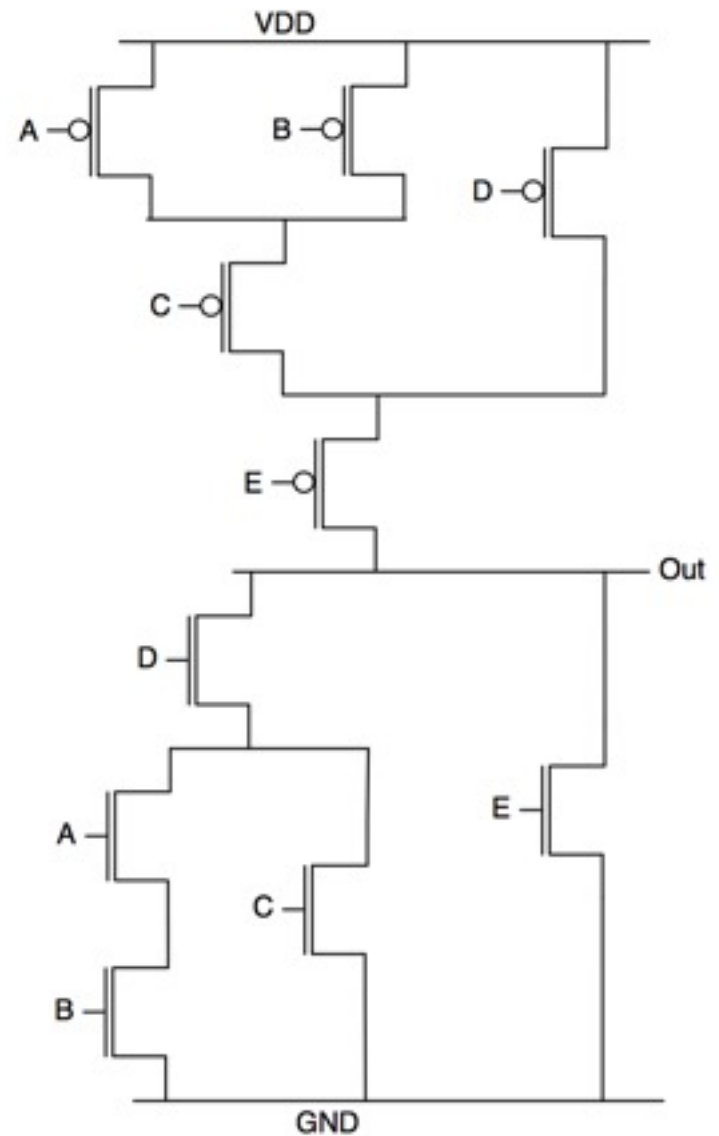


# Gate sizing example – XNOR



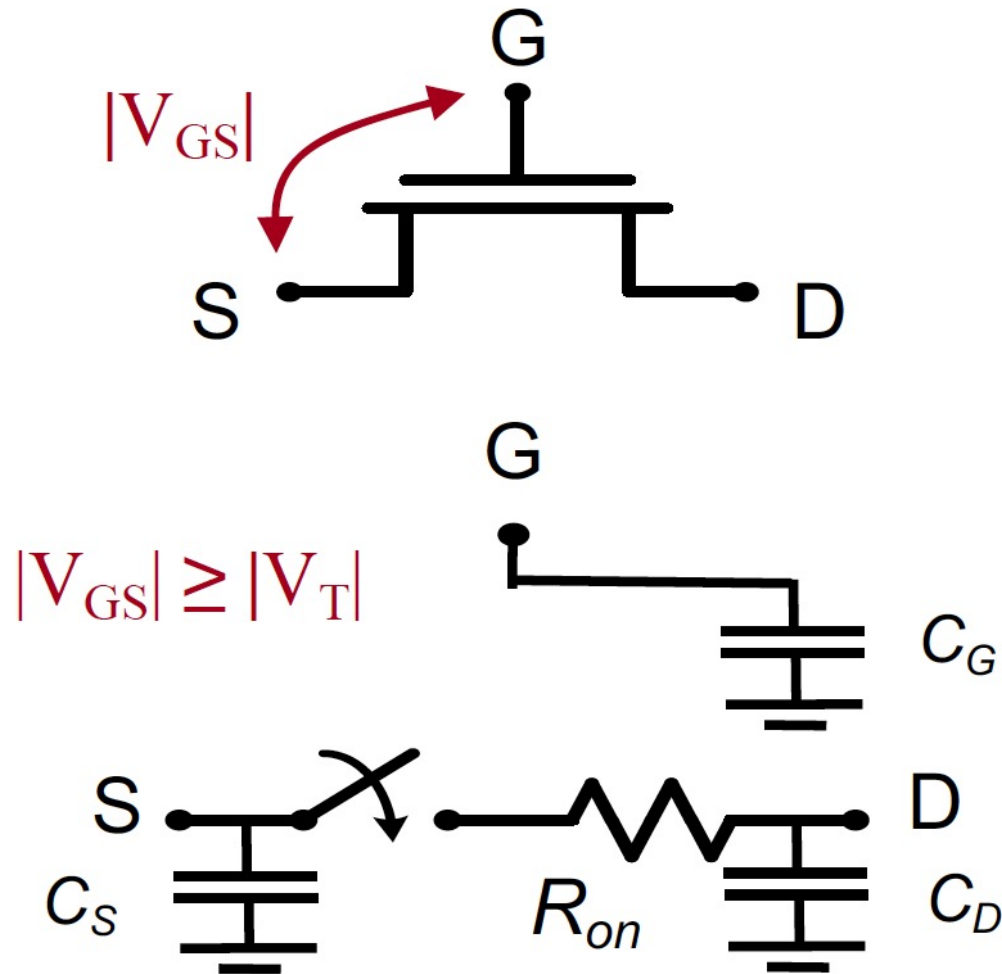
# Gate sizing example

$$R_{on,p} = 3 * R_{on,n}$$

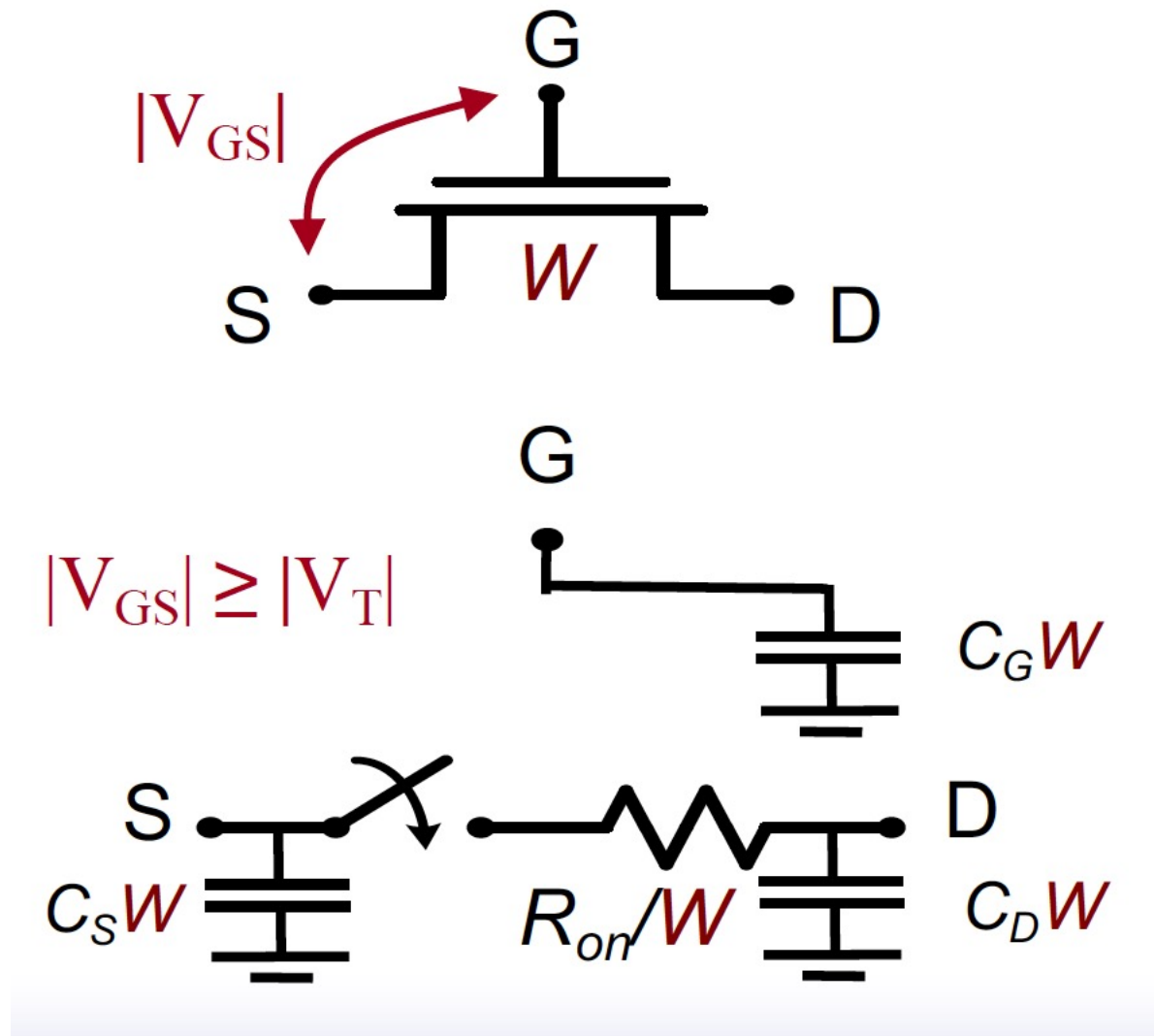


# Inverter delay

# Simple dynamic model

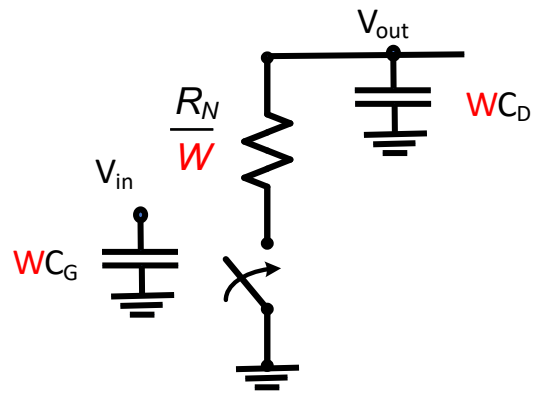


# Simple dynamic model

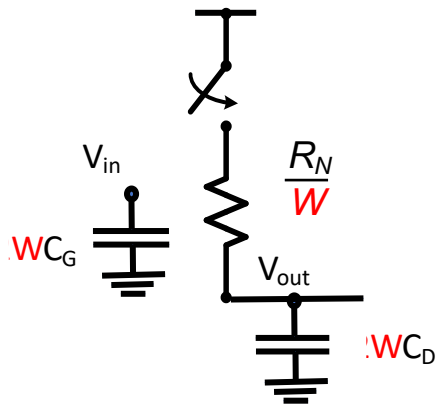




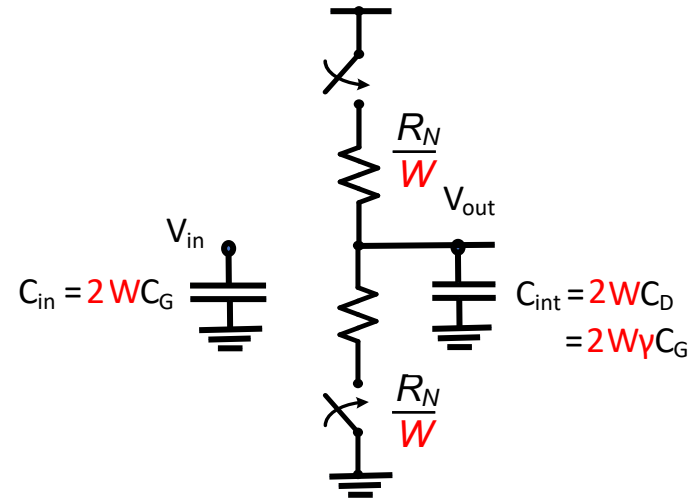
# Inverter delay



NMOS with size  $W$



PMOS with same  $R$  as NMOS



# Inverter fanout

